

**UT3400***Power MOSFET***N-CHANNEL ENHANCEMENT
MODE POWER MOSFET****DESCRIPTION**

The UTC **UT3400** is an N-ch enhancement MOSFET providing the customers with perfect $R_{DS(ON)}$ and low gate charge. This device can be operated with 2.5V low gate voltage.

The UTC **UT3400** is optimized for applications, such as a load switch or in PWM.

FEATURES

* V_{DS} (V)=30V

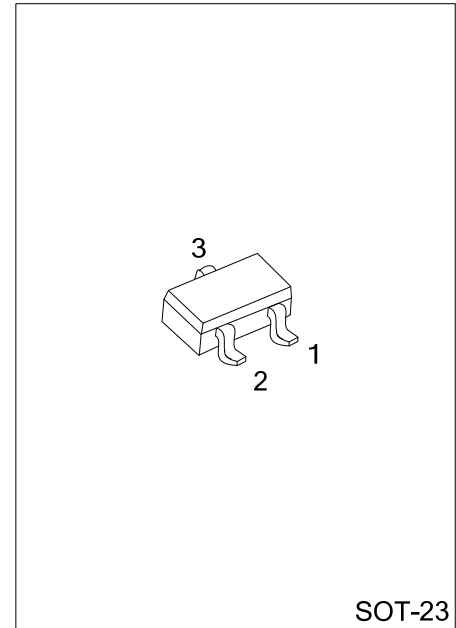
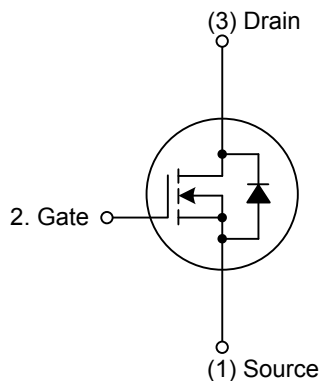
* I_D =5.8 A

* $R_{DS(ON)} < 28m\Omega$ @ $V_{GS}=10V$

$R_{DS(ON)} < 33m\Omega$ @ $V_{GS}=4.5V$

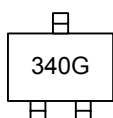
$R_{DS(ON)} < 52m\Omega$ @ $V_{GS}=2.5V$

* Halogen Free

SYMBOL**ORDERING INFORMATION**

Ordering Number	Package	Pin Assignment			Packing
		1	2	3	
UT3400G-AE3-R	SOT-23	S	G	D	Tape Reel

UT3400G-AE3-R (1)Packing Type (2)Package Type (3)Halogen Free	(1) R: Tape Reel (2) AE3: SOT-23 (3) G: Halogen Free
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MARKING

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	5.8	A
Pulsed Drain Current (Note 2)	I_{DM}	30	A
Power Dissipation	P_D	1.4	W
Junction Temperature	T_J	+150	°C
Storage Temperature	T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Pulse width limited by $T_{J(MAX)}$

3. Pulse width $\leq 300\mu s$, duty cycle $\leq 0.5\%$.

■ THERMAL DATA

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT
Junction to Ambient (Note)	θ_{JA}		85	125	°C/W

Note: Surface mounted on 1 in² copper pad of FR4 board with 2oz

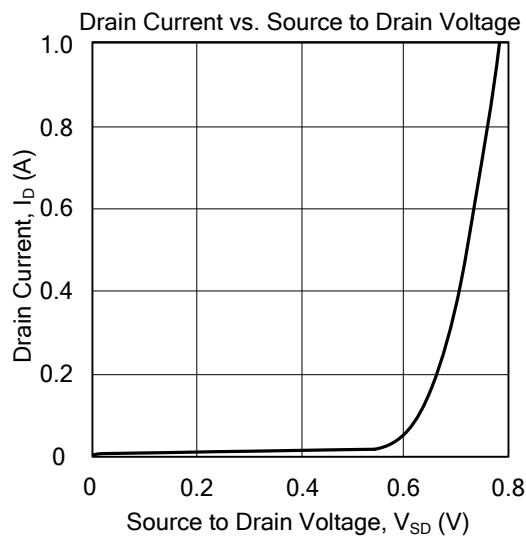
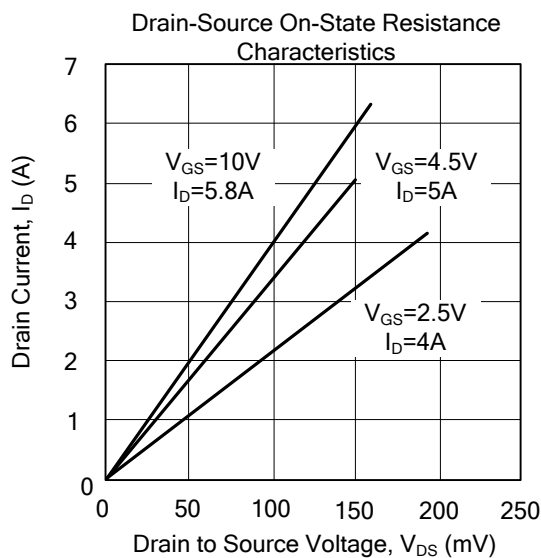
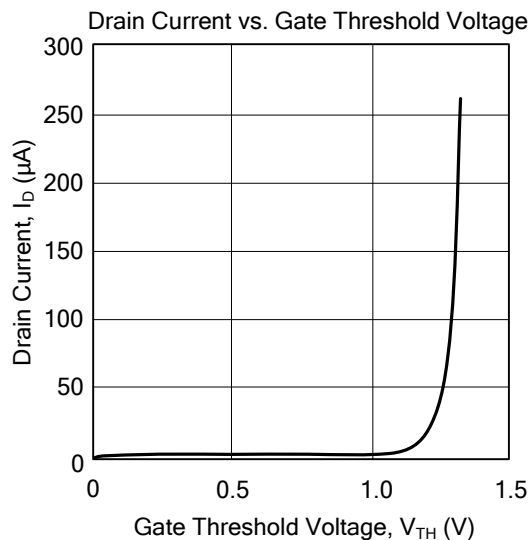
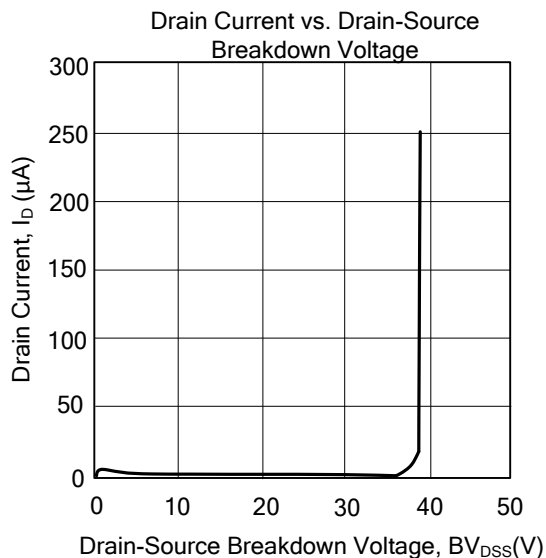
■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	30			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =24V, V _{GS} =0V			1	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±12V, V _{DS} =0V			100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	0.7	1.1	1.4	V
On-State Drain Current	I _{D(ON)}	V _{DS} =5V, V _{GS} =4.5V	30			A
Drain to Source On-state Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =5.8A		22.8	28	mΩ
		V _{GS} =4.5V, I _D =5A		27.3	33	mΩ
		V _{GS} =2.5V, I _D =4 A		43.3	52	mΩ
DYNAMIC PARAMETERS						
Input Capacitance	C _{ISS}	V _{DS} =15V, V _{GS} =0V, f =1MHz		823		pF
Output Capacitance	C _{OSS}			99		pF
Reverse Transfer Capacitance	C _{RSS}			77		pF
Gate Resistance	R _G	V _{GS} =0V, V _{DS} =0V, f =1MHz		1.2		Ω
SWITCHING PARAMETERS						
Turn-ON Delay Time	t _{D(ON)}	V _{GS} =10V, V _{DS} =15V R _L =2.7Ω, R _{GEN} =6Ω		5.5		ns
Turn-ON Rise Time	t _R			5.1		ns
Turn-OFF Delay Time	t _{D(OFF)}			37		ns
Turn-OFF Fall-Time	t _F			4.2		ns
Total Gate Charge	Q _G	V _{GS} =4.5V, V _{DS} =15V, I _D =5.8A		9.7		nC
Gate Source Charge	Q _{GS}			1.6		nC
Gate Drain Charge	Q _{GD}			3.1		nC
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Voltage	V _{SD}	I _S =1A, V _{GS} =0V		0.71	1	V
Diode Continuous Forward Current (Note 1)	I _S				2.5	A
Reverse Recovery Time	t _{RR}	I _F =5A, dI/dt=100A/μs		16		ns
Reverse Recovery Charge	Q _{RR}			8.9		nC

Notes: 1. Pulse width limited by $T_{J(MAX)}$

2. Pulse width $\leq 300\mu s$, duty cycle $\leq 0.5\%$.

■ TYPICAL CHARACTERISTICS



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